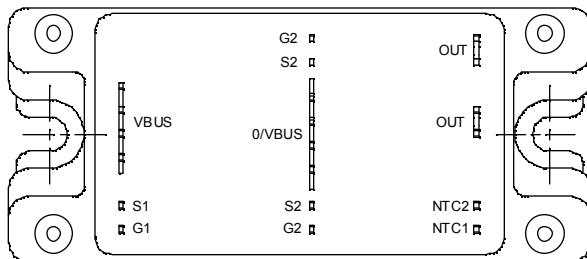
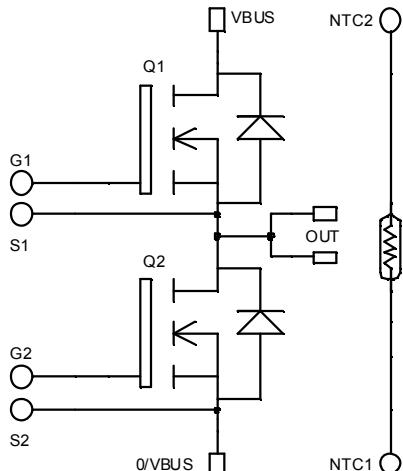


Phase leg MOSFET Power Module

V_{DSS} = 100V
R_{DSon} = 4.5mΩ typ @ T_j = 25°C
I_D = 278A @ T_c = 25°C



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS V® FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage	100	V
I _D	Continuous Drain Current	T _c = 25°C	A
		T _c = 80°C	
I _{DM}	Pulsed Drain current	1100	
V _{GS}	Gate - Source Voltage	±30	V
R _{DSon}	Drain - Source ON Resistance	5	mΩ
P _D	Maximum Power Dissipation	T _c = 25°C	W
I _{AR}	Avalanche current (repetitive and non repetitive)	100	A
E _{AR}	Repetitive Avalanche Energy	50	mJ
E _{AS}	Single Pulse Avalanche Energy	3000	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}$, $V_{DS} = 100\text{V}$	$T_j = 25^\circ\text{C}$			200	μA
		$V_{GS} = 0\text{V}$, $V_{DS} = 80\text{V}$	$T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}$, $I_D = 125\text{A}$			4.5	5	$\text{m}\Omega$
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 5\text{mA}$		2		4	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{ V}$, $V_{DS} = 0\text{V}$				± 200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$			20		nF
C_{oss}	Output Capacitance				8		
C_{rss}	Reverse Transfer Capacitance				2.9		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 50\text{V}$ $I_D = 250\text{A}$			700		nC
Q_{gs}	Gate – Source Charge				120		
Q_{gd}	Gate – Drain Charge				360		
$T_{d(on)}$	Turn-on Delay Time		Inductive switching @ 125°C		80		ns
T_r	Rise Time	$V_{GS} = 15\text{V}$			165		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 66\text{V}$			280		
T_f	Fall Time	$I_D = 250\text{A}$	$R_G = 2.5\Omega$		135		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C			1.1		mJ
E_{off}	Turn-off Switching Energy	$V_{GS} = 15\text{V}$, $V_{Bus} = 66\text{V}$	$I_D = 250\text{A}$, $R_G = 2.5\Omega$		1.2		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C			1.22		mJ
E_{off}	Turn-off Switching Energy	$V_{GS} = 15\text{V}$, $V_{Bus} = 66\text{V}$	$I_D = 250\text{A}$, $R_G = 2.5\Omega$		1.28		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit	
I_S	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$			278	A	
			$T_c = 80^\circ\text{C}$			207		
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = - 250\text{A}$				1.3	V	
dv/dt	Peak Diode Recovery ①					5	V/ns	
t_{rr}	Reverse Recovery Time	$I_S = - 250\text{A}$ $V_R = 50\text{V}$ $di_S/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$			190	ns	
			$T_j = 125^\circ\text{C}$			370		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		0.8		μC	
			$T_j = 125^\circ\text{C}$		3.4			

 ① dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq - 278\text{A}$ $di/dt \leq 200\text{A}/\mu\text{s}$ $V_R \leq V_{DSS}$ $T_j \leq 150^\circ\text{C}$



Thermal and package characteristics

Symbol Characteristic

Min Typ Max Unit

R _{thJC}	Junction to Case Thermal Resistance				0.16	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I isol < 1mA, 50/60Hz			2500		V
T _J	Operating junction temperature range			-40	150	
T _{STG}	Storage Temperature Range			-40	125	
T _C	Operating Case Temperature			-40	100	
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

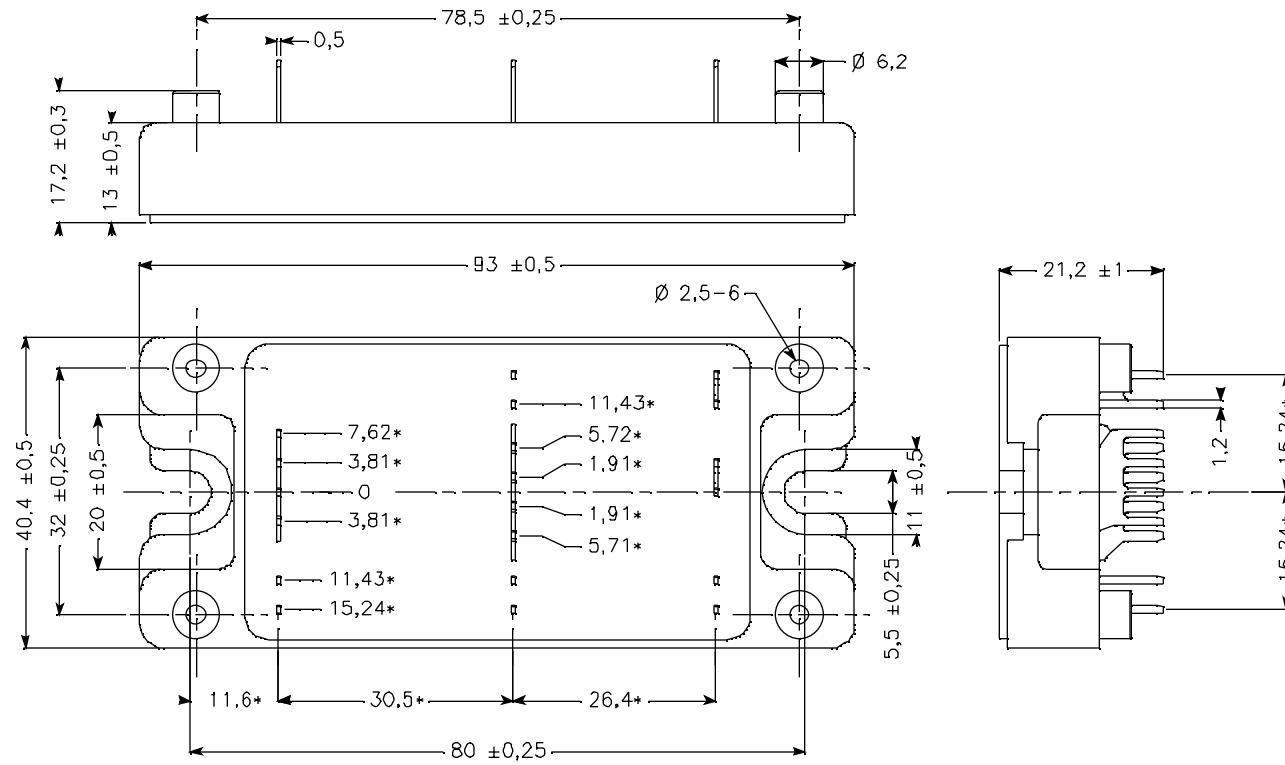
Symbol Characteristic

Min Typ Max Unit

R ₂₅	Resistance @ 25°C				50	kΩ
B _{25/85}	T ₂₅ = 298.15 K				3952	K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]} \quad \begin{array}{l} T: \text{Thermistor temperature} \\ R_T: \text{Thermistor value at } T \end{array}$$

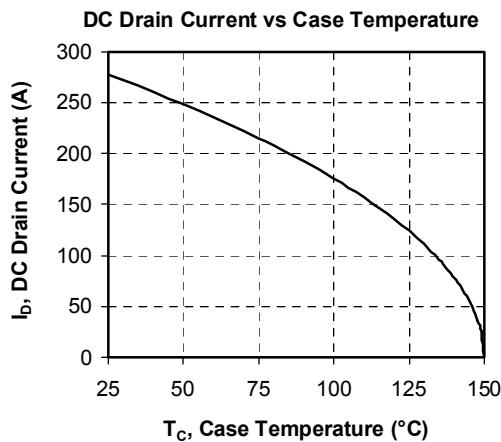
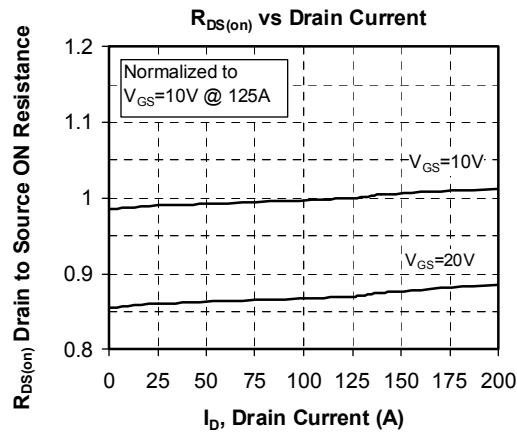
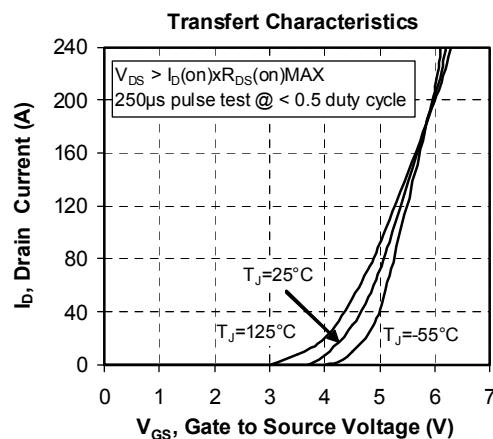
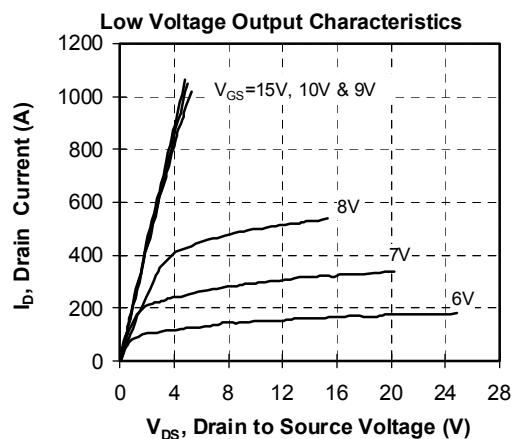
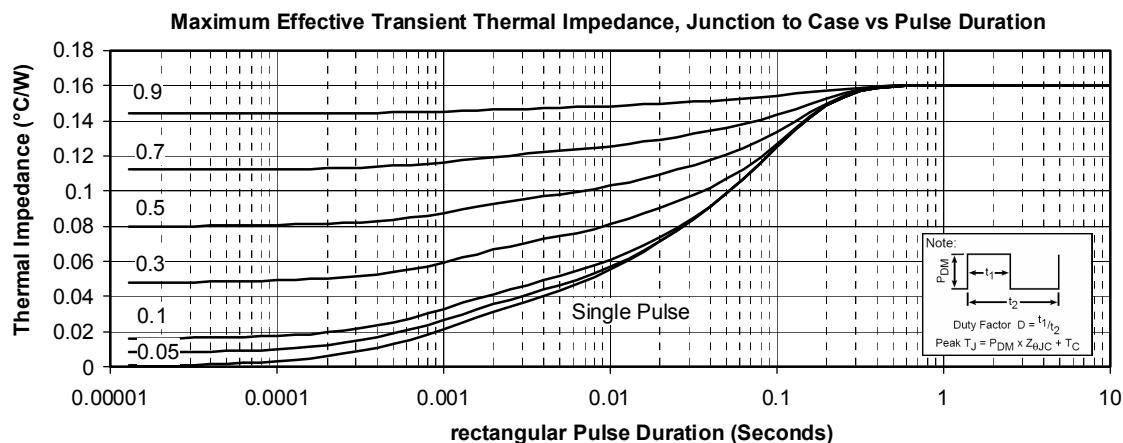
SP4 Package outline (dimensions in mm)

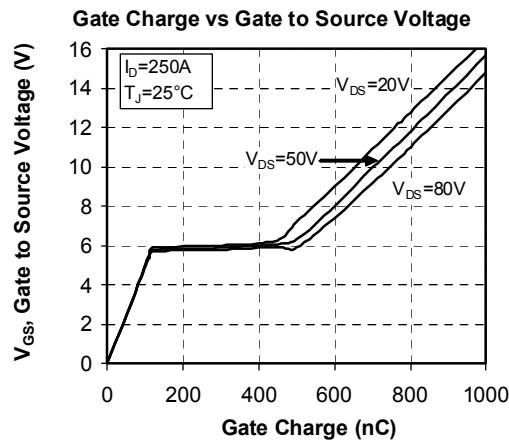
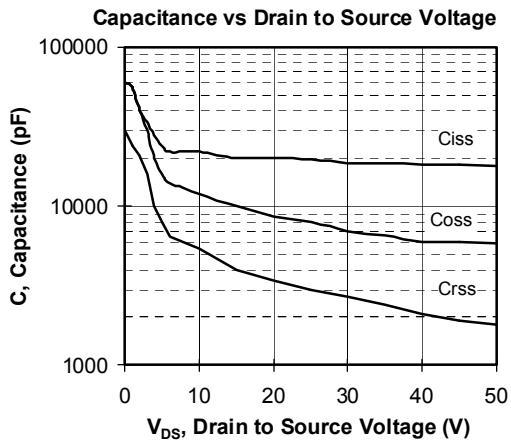
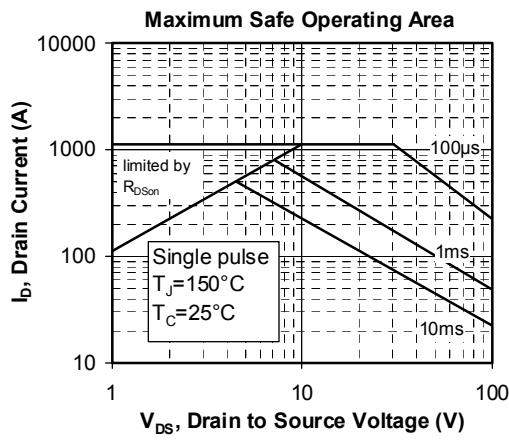
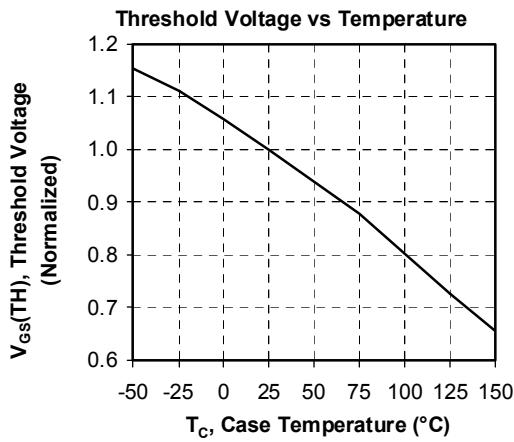
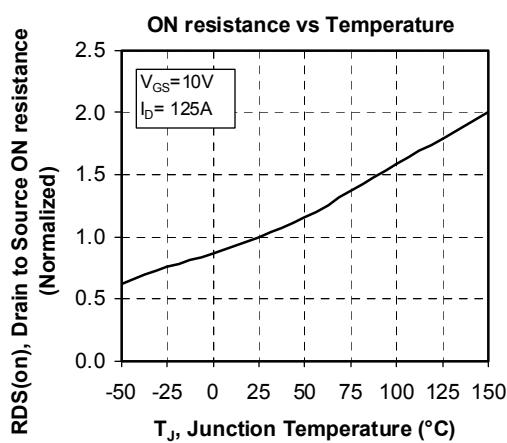
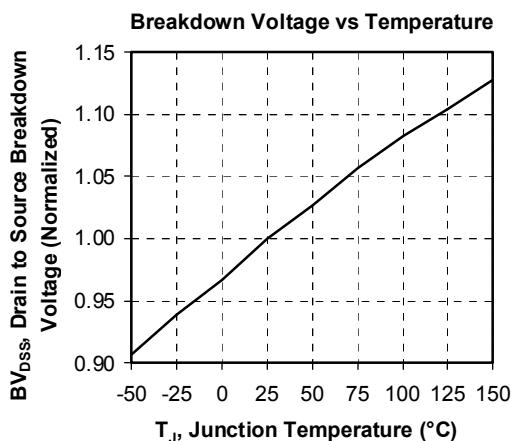


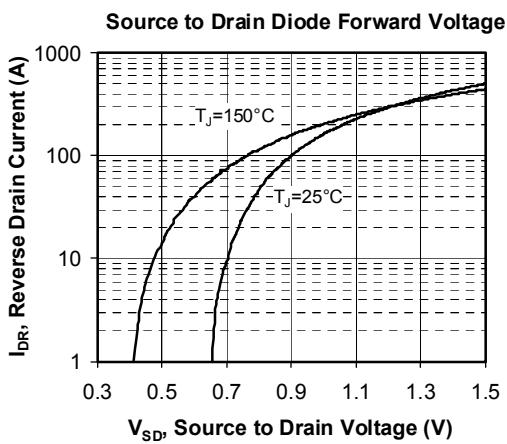
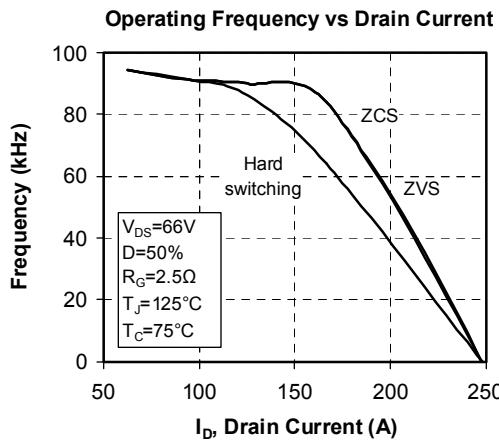
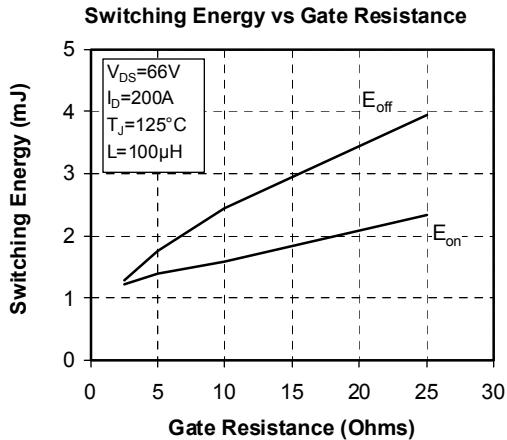
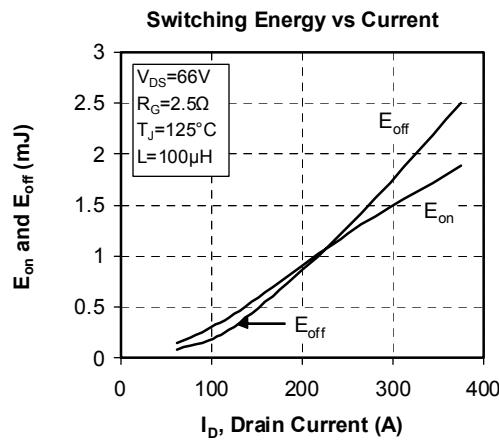
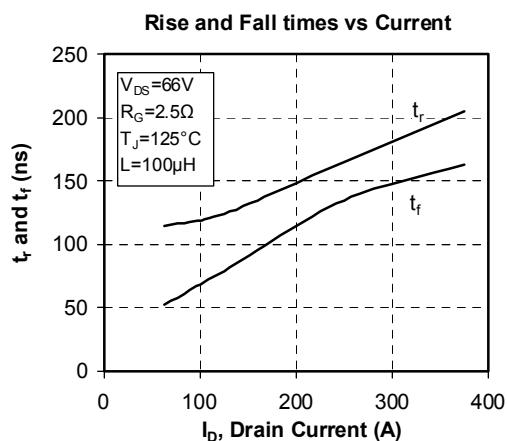
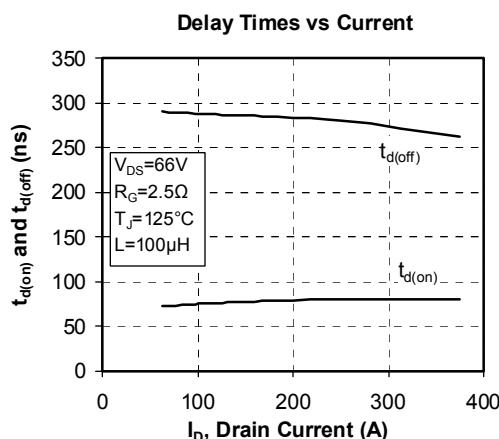
ALL DIMENSIONS MARKED " * " ARE TOLERENCED AS : ± 0.25

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve







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Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литер Н,
помещение 100-Н Офис 331